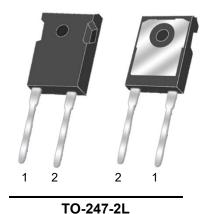




Schoktty Barrier Diode

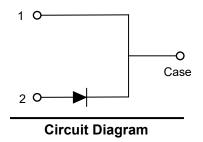
Feature

- ➤ Low conduction loss due to low V_F
- > Extremely low switching loss by tiny Q_C
- ➤ Negligible reverse recovery
- > Positive Temperature Coefficient
- ➤ Pb-free / RoHS compliant
- > Highly rugged due to better surge current
- ➤ High-reliability



Applications

- Solar inverters
- > Uninterruptable power supplies
- Motor drives
- > Power Factor Correction



Absolute maximum rating@25°C

Parameter			Value	Units
Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
Continuous Forward Current	T _c =145°C	I _{F(AVG)}	50*	Α
Non-repetitive Forward Surge Current	T _c =25°C,t _p =10ms,Half Sine Pulse	I _{FSM}	280	Α
Power Dissipation	T _c =25°C	Б	457*	W
	T _c =110°C	P _{tot}	198*	
Operating Junction Range		T _J	-55~+175	°C
Storage Temperature Range		T _{STG}	-55~+175	°C

^{*} Assumes thermal resistance of 0.328°C/W or less

Schoktty Barrier Diode

PSICS2TAF1200V50N

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
DC blocking voltage	V _{DC}	T _J =25°C	1200	-	-	V
Forward Voltage	V _F	I _F = 50A, T _J =25°C	-	1.48	-	V
		I _F = 50A, T _J =175°C	-	2.17	-	
Reverse Current	I _R	V _R = 1200V, T _J =25°C	-	8	-	μA
		V _R = 1200V, T _J =175°C	-	54	-	
Total Capacitive Charge	Q _C	$V_R = 800V, T_j = 25^{\circ}C,$ $Q_C = \int_0^{V_R} C(V) dV$	-	326	-	nC
Total Capacitance	С	$V_R = 1V, f = 1MHz$	-	3571	-	pF
		V _R = 400V,f = 1MHz	-	307	-	
		V _R = 800V,f = 1MHz		231	-	
Capacitance stored energy	E _C	V _R = 800V	-	93	-	μJ

Typical Characteristics

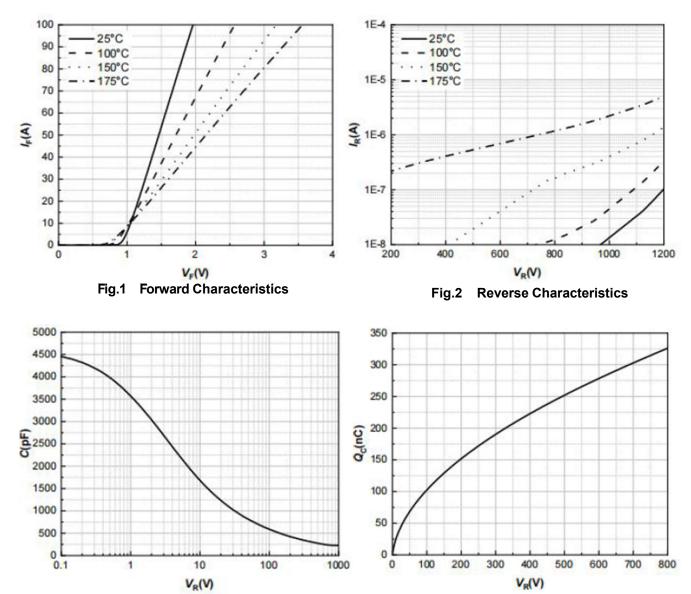
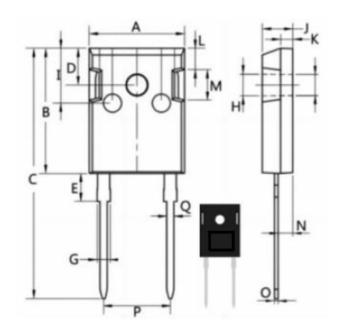


Fig.3 Capacitance Charge vs. Reverse Voltage

Fig.4 Reverse Charge vs. Reverse Voltage

Schoktty Barrier Diode

Product dimension (TO-247-2L)



Dim	Millimeters			
Dim	Min	Max		
Α	15.5	15.7		
В	20.35	20.55		
С	20.45	20.85		
D	5.89	6.17		
E	4.14	4.45		
G	1.13	1.19		
Н	4.45	4.55		
I	8.15	8.60		
J	4.95	5.05		
К	1.96	1.99		
L	3.24	3.72		
M	4.625	4.725		
N	2.35	2.41		
0	0.592	0.608		
Р	1.13	1.18		

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